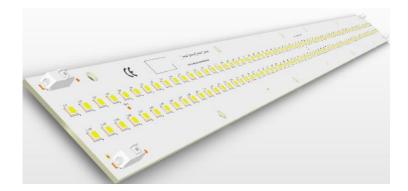


## SunLike Linear Reference Module

#### **Product Overview:**

- Zhaga standard mounting pattern
- Uniformity of light and color.
- Best in class efficacy at typical driving currents



## **Lighting Applications:**



#### Features:

- High Color Quality with CRI Min.95.
- Industry standard mechanical attributes
- Optimized to function with industry standard power supplies
- 3 SDCM
- ROHS compliant



#### **Applications:**

- Residential
- Commercial
- Linear highbay

#### Product Selection - SMJD-4846144G-XXN1 I<sub>F</sub> = 900mA, Ta= 25°C

ССТ	CRI	FI	ux	Length	Order Code	
		Min	Тур.			
2700	95	3600	3800	560*39.8	SMJD-4846144G-XXN1 00D80H039All	
3000	95	3600	3800	560*39.8	SMJD-4846144G-XXN1 00D80G039All	
4000	95	4000	4200	560*39.8	SMJD-4846144G-XXN1 00E20E039All	
5000	95	4000	4200	560*39.8	SMJD-4846144G-XXN1 00E20C039All	



#### Maximum Operating Specification: Ta = 25°C

Model	Parameter	Symbol	Unit	Value	Remark
	Power Consumption	Р	W	70	
SMJD-4846144G-XXN1	Driving Current	١ <sub>F</sub>	mA	1350	
SMJD-4846144G-XXN1	Operating Temperature <sup>(3)</sup>	Tc	٥C	- 40 ~ 98	Reference point
SMJD-4846144G-XXN1	Storage Temperature	Tc <sub>tg</sub>	٥C	- 40 ~ 98	With no power
	Thermal resistance	D	00.004	0.0	
SMJD-4846144G-XXN1	(T <sub>c</sub> to base)	umptionPWurrentIFmAoperature (3)T_C°CoperatureTctg°Csistance $R_{th(Tc-base)}$ °C/V	°C/VV	0.3	
				±8	IEC Air
SMJD-4846144G-XXN1	ESD Sensitivity	-	٣V	±4	НВМ

## Electro Optical Characteristics , SMJD-4846144G-XXN1 $I_F = 900 \text{mA} T_a = 25^{\circ}C^{(1)}$

Deremeter			Value				
Parameter	Symbol	Min.	Тур.	Max.	Unit	Remark	
Luminous Flux	♠ [2]	3600	3800	-		H,G	
Luminous Flux	Φ <sub>V</sub> <sup>[2]</sup>	4000	4200	-	— Im —	E,C	
		4700	5028	5300		С	
Correlated Color		3700	3985	4200	– к –	E	
Temperature <sup>[3]</sup>	ССТ	2900	3045	3200	- r -	G	
		2600	2725	2900		н	
CRI	Ra	95	-	-	-	-	
Input Voltage	V <sub>F</sub>	48	52	56	V <sub>DC</sub>	@ <b>0</b> 00	
Power Consumption	Р	42	46	50	W	@900mA	
Efficiency		-	90	-		H,G	
Efficiency	LPW	-	95	-	– Lm/W –	E,C	

#### Notes:

1 Above data tested with constant typical current at  $T_a = 25^{\circ}$ C.

2  $\Phi_V$  is the total luminous flux output measured with an integrated sphere.

3 Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.

4 To use the module properly, recommend to drive the module by a Constant Current Source (CCS). But the Maximum output voltage of the CCS should be limited by referring this sheet.

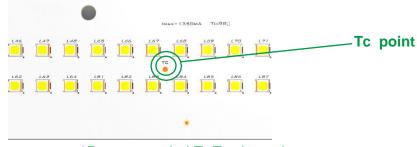


Notes:

\*The color of engines are fully comply with the CIE requested color temperature as the following listed table.

Correlated Color Temperature	Nominal CCT	CCT (K)
C	5000 K	5028 ± 283
E	4000 K	3985 ± 275
G	3000 K	3045 ± 175
Н	2700 K	2725 ± 145

#### ILLUSTRATION 1: How to predict components temperature [4]



Notes :

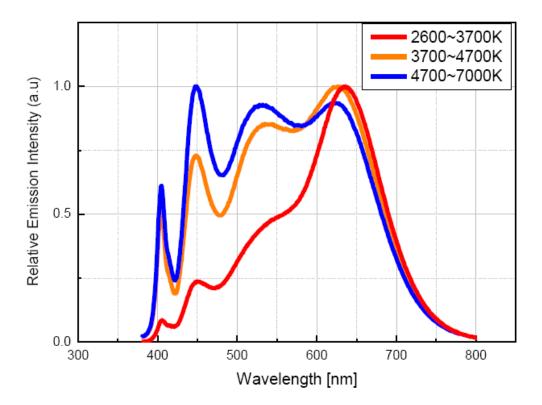
\*Recommended Tc Testing point

- (1) All guarantee are based on the Absolute Maximum Ratings listed.
- (2) Please use a Constant Current Source (CCS) to drive the module, the typical V<sub>F</sub> of module is 52 VDC and  $V_{F_{-MAX}}$  is 56 VDC, respectively.
- (3) Operating temperature was tested at the assigned Tc point on the PCB.
- (4) To ensure the module works properly, Tc should be kept below 98 °C;



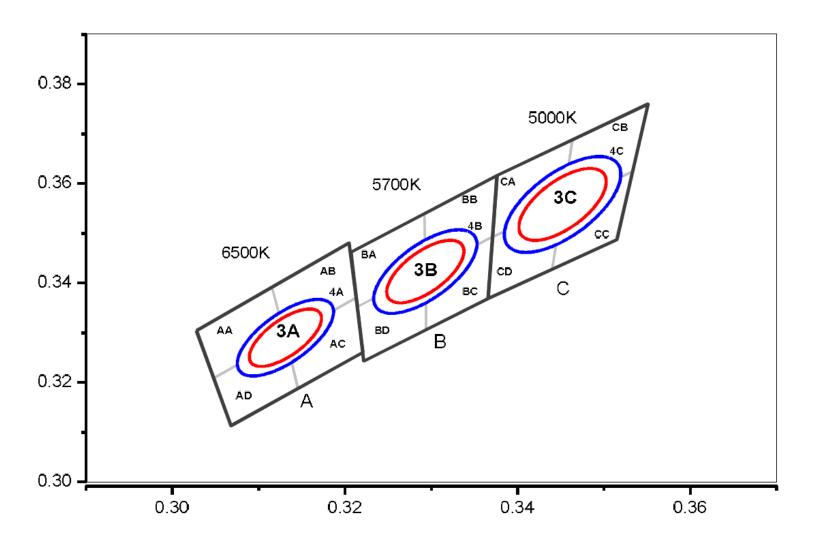
## **Relative Spectral Distribution**

Relative Spectral Distribution vs. Wavelength





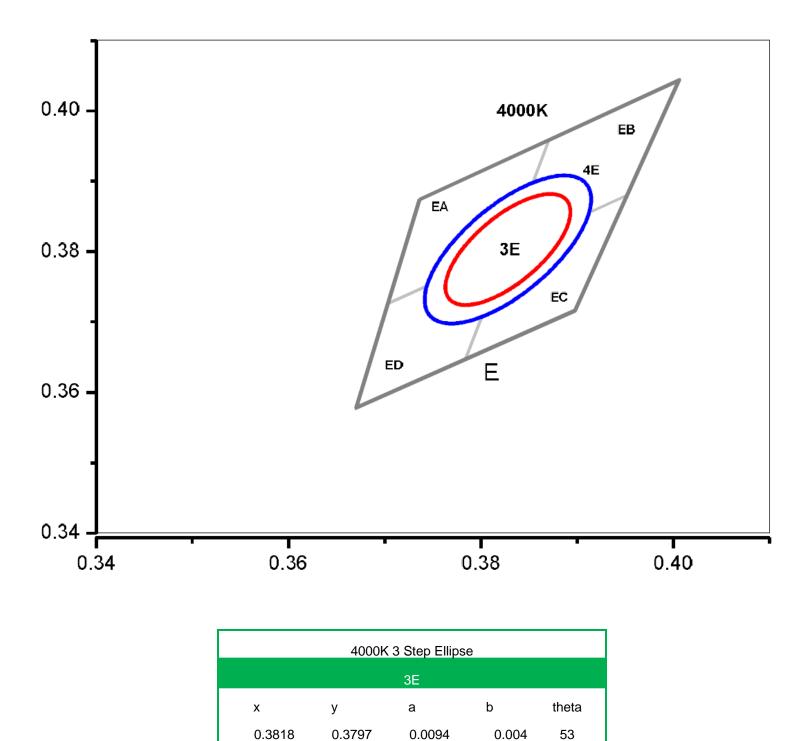
• CIE Chromaticity Diagram (Cool white), T<sub>a</sub>=25°C



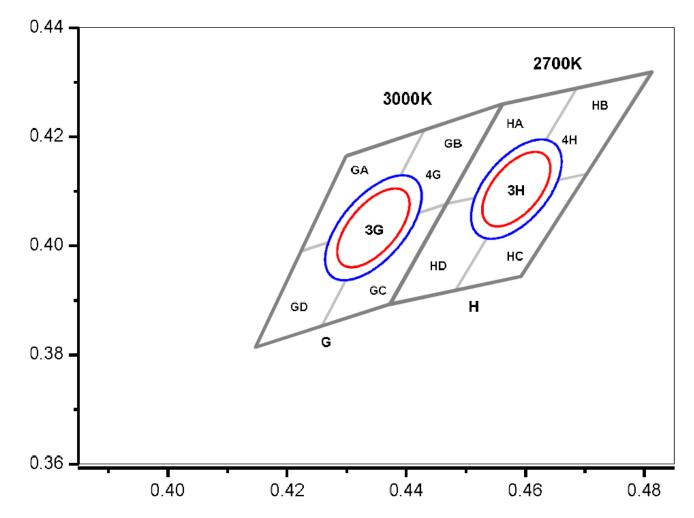
	6500K 3 Step Ellipse 5700K 3 Step Ellipse							5000K 3 Step Ellipse						
	3A 3B					3C								
х	у	а	b	theta	х	у	а	b	theta	х	у	а	b	theta
0.3123	0.3282	0.0066	0.0027	58	0.3287	0.3417	0.0071	0.0030	59	0.3447	0.3553	0.0081	0.0035	60



• CIE Chromaticity Diagram (Cool white), T<sub>a</sub>=25°C



SEOUL SEMICONDUCTOR



• CIE Chromaticity Diagram (Cool white), T<sub>a</sub>=25°C

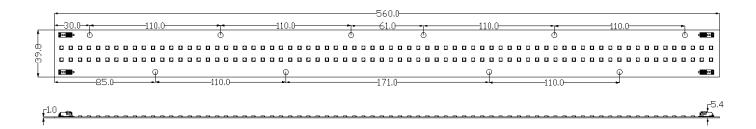
SEOUL

	3000K 3	3 Step Ell	ipse	2700K 3 Step Ellipse					
		3G					3H		
х	у	а	b	theta	х	у	а	b	theta
0.4338	0.4030	0.0085	0.0041	53	0.4578	0.4104	0.0079	0.0041	54

## **Mechanical Dimensions**

#### • SMJD-4846144G-XXN1

Dimension	Specification	Tolerance	Unit
Module Length	560	±0.5	mm
Module Width	39.8	±0.3	mm
Module Height	5.4	±0.3	mm
PCB Thickness	1.0	±0.1	mm
Module weight	TBD	±10	g



## **Product Nomenclature:**

\*Please refer to the following chart

Seoul DC Module	<u>SM</u> —(1	<u>JD</u>	- <u>48</u> 2	<u>46</u> 3	<u>144</u> (4)	<u>G</u> - 5	<u>XX</u> 6	<u>N</u> (7)	<u>1</u> ⑧	
Volta	ige	Pov	ver		LED Qty		Туре	Custom	Dimming	Etc
4	8	4	6	1	4	4	G	XX	N	1
<b>0</b> <i>OV</i>	0 ov	<b>0</b> <i>ow</i>	<b>0</b> ow	<b>0</b> 0ea	<b>0</b> 0ea	<b>0</b> 0ea	<b>C</b> 3030	XX ref	N Norm	1 vers
<b>1</b> 10V	<b>1</b> 1V	<b>1</b> 10W	<b>1</b> 1W	<b>1</b> 100ea	<b>1</b> 10ea	<b>1</b> 1ea			D Dim	
<b>2</b> 20V	<b>2</b> 2V	<b>2</b> 20W	<b>2</b> 2W	<b>2</b> 200ea	<b>2</b> 20ea	<b>2</b> 2ea			E etc	
<b>3</b> 30V	<b>3</b> 3V	<b>3</b> 30W	<b>3</b> 3W	<b>3</b> 300ea	<b>3</b> 30ea	<b>3</b> 3ea				
-	-	-	-	-	-	-				
<b>9</b> 90V	<b>9</b> 9V	<b>9</b> 90W	<b>9</b> 9W	<b>9</b> 900ea	<b>9</b> 90ea	<b>9</b> 9ea				
<b>A</b> 100V		<b>A</b> 100W		<b>A</b> 1000ea						
<b>B</b> 110V		<b>B</b> 110W		<b>B</b> 1100ea						
-		-		-						
<b>Z</b> 350V		<b>Z</b> 350W		<b>Z</b> 3500ea						

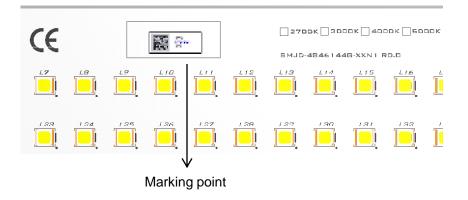
## **Product Nomenclature: Binning**

\*Please refer to the following chart

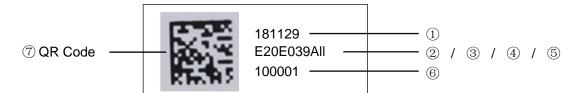
	<u>00</u> (A)	<u>E20</u> <u>E03</u> <u>9</u> (B) (C) (D	(E)	
Lens Type	Flux Bin	CCT Bin	CRI Bin	VF Bin
00	D30	E03	8	All
00 No Lens	<b>D80</b> 3800 lm	<b>H03</b> 2700k – 3step	<b>9</b> CRI 95	<b>All</b> 48~56V <sub>DC</sub>
	<b>D80</b> 3800 lm	<b>G03</b> 3000k – 3step		
	<b>E20</b> 4200 <i>lm</i>	<b>E03</b> 4000k – 3 step		
	<b>E20</b> 4200lm	<b>C03</b> 5000k – 3 step		



#### **Marking Information**



Marking Information

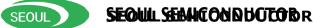


No.	ltem	Information		DigiTc	Remark				
1	Date		YYMMDD		YYMMDD		YYMMDD		SMT date
2	Flux <sup>(1)</sup>	E20		3Digit	E20=4200lm <sup>(1)</sup>				
3	CCT	X03 3-step Mixing		3Digit	X=C,E,G,H				
4	CRI		9		CRI=95				
5	V <sub>F</sub>		All	3Digit					
	Lot No.		1	1 Digit	0~9,A~Z				
6	Sequence No.		00001	5 Digit	00001 ~ 99999				
$\overline{O}$	QR Code	QR Code		-	Please refer bellow table				

#### Note:

(1) Flux bin please refer to the bellow binning definitions

Symbol	lm	Symbol	lm	Symbol	lm	Symbol	lm
A20	200	D20	3200	G20	6200	J20	9200
B20	1200	E20	4200	H20	7200	K20	10200
C20	2200	F20	5200	120	8200	L20	11200



#### Module QR Code Information

	QR Code Information											
Items	Factory	SAP Code	SMT Date	Characteristics	Line No.	Lot No.	Serial number	Note				
Digits	1 Digit	7 Digits	6 Digits	10 Digits	1 Digit	1 Digit	5 Digits	In Total				
Information	1~9	*****	YYMMDD	E20E039All	1~9, A~Z	1~9, A~Z	00001	31 Digits				

Notes:

- 1 QR coded information shall include the fields described in the table above.
- 2 Minimum size of QR code shall be 4.5 mm x 4.5 mm and a minimum QR code grade of 'C'. \*'A' grading is preferred.
- 3 If the component is small to have a full label, it is acceptable to have only the QR code in minimum size of 6 mm by 6 mm printed on a label.
- 4 Each character is separated by "," Example: SMJD-4846144G-XXN1, XXXXXX, 181129, 00E20E039AII, 1, 1, 1, 00001

#### **Label Information**

Model No.	SMJD-4846144G-XXN1 <sup>[1]</sup> IIIII II IIIII III
Rank	E20E039ALL <sup>[2]</sup> IIIII II IIIII III
Туре	Standard
Quantity	XXX 
Lot No.	YYMDDXXXXX- XXXXXXX <sup>[3]</sup> IIIII II IIIII III
SEOUL	SEOUL SEMICONDUCTOR CO.,LTD.

#### Notes:

[1] & [2] Please refer to page 9.

[3] Initial of manufacture is refer to the 2D code rule.

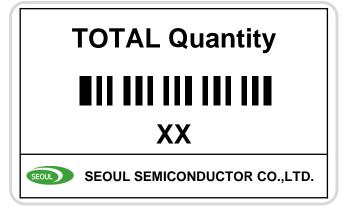
YYMDD : Packing Date (Oct. : A, Nov. : B, Dec. : C)

X =Initial of Manufacturer

XXXX = Sealing Pack No.

XXXXXXX =SSC Code

[4] It is attached to the top right corner of the carton box

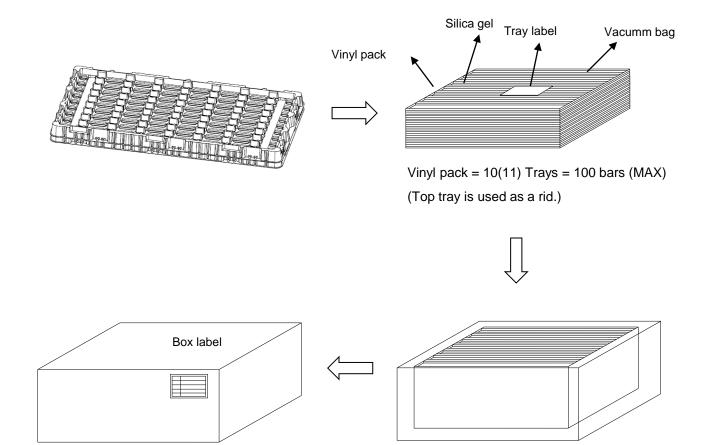


#### Notes:

[1] Attached to the bottom left corner of the carton box.



#### **Packaging Specification**



1 Box = 10(11) Trays = 100bars (MAX)

Model	Тгау		Box		Pallet	
	Size(mm)	Q'TY per Tray	Size(mm)	Q'TY per Box	Size(mm)	Q'TY per Pallet
SMJD-4846144G-XXN1	610 x 300 x 30	10	625*315*215	100	1000*1000	1800



## **Precaution for Use**

- 1. Check the appearance of engine before wiring/ assembly, DO NOT use the lens cracked or wire damaged engine.
- 2. The engine was designed to be driven with DC source, recognize the polarities of the engine was necessity.
- 3. It was not SELV engine, DO NOT connect the LED driver to main power during wiring.
- 4. DO NOT prolong the cable too much for long term using
- 5. No current regulator built in engine, unevenly load between different parallel engines may occur due to the engines VF variance.
- 6. DO NOT detach the lens at any application.
- 7. DO NOT let the lens face to touch rough stuff, and DO NOT touch lens with sharp matters
- 8. Please do not use together with the materials containing Sulfur.
- 9. Please do not make any modification on module.
- LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
  The following contains suggestions that Seoul Semiconductor purposes to minimize these effects
  - A. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two object come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- · Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event: One or more recommended work area suggestions:

- Ionizing fan setup
- · ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- · Antistatic wrist-strap
- Antistatic material shoes
- · Antistatic clothes

Environmental controls:

- · Humidity control (ESD gets worse in a dry environment)
- B. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

•Changes to the performance of the LED package (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)

- Changes to the light output of the luminaire from component failure
- ·Components on the board not operating at determined drive power
- Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures

It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred.

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse).
- · Damage to the bond pads located on emission surface of the LED package (shadowing can be noticed around the bond pads viewing through microscope).
- Anomalies noticed in encapsulation & phosphor around bond wires. This damage usually appears due to thermal stress produced during EOS event.
- C. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing
  - · Qualified LED driver with no big over shoot out put · Isolated driver that to prevent harmful peaks passed to engine. A current limiting device



#### Storage before use

- 1. DO NOT impact or place pressure on this product because even a small amount of pressure can damage the lens cover.
- 2. When storing devices for a long period of time before usage, please following these guidelines.
  - The devices should be stored in the anti-static bag that it was shipped in from Seoul-Semiconductor with opening
    - If the anti-static bag has been opened, re-seal preventing air and moisture from being present in the bag.



# SEOUL SEMICONDUCTOR

#### **Company Information**

Seoul Semiconductor (SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotice, general illumination/ lighting, appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", deep UV LEDs, "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology", a proprietary family of high-voltage LEDs. The company's broad product portfolio includes a wide array of package and device choices such as Acrich, high-brightness LEDs, mid-power LEDs, side-view LEDs, through-hole type LED lamps, custom displays, and sensors. The company is vertically integrated from epitaxial growth and chip manufacture in it's fully owned subsidary, Seoul Viosys, through packaged LEDs and LED modules in three Seoul Semiconductor manufacturing facilities. Seoul Viosys also manufactures a wide range of unique deep-UV wavelength devices.

#### Legal Disclaimer

Information in this document is provided in connection with Seoul Semiconductor products. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Seoul Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party. The appearance and specifications of the product can be changed to improve the quality and/or performance without notice.